

**IN THE SPECIFICATION:**

Replace the paragraph beginning on line 25 of page 1 with the following:

Each of the input/output pads 22 is typically ~~shaped to have a~~ square ~~shaped with a side of~~ having sides approximately 100 ~~in~~ μm in length. Due to limitations of mechanical accuracy of a bonding apparatus for use in a wire bonding process, it is difficult to significantly reduce the input/output pads 22 in size. Thus, when the required number of input/output pads 22 are arranged in the periphery of the rectangular chip 20 as shown in Fig. 5, the minimum chip size is accordingly determined.

Replace the first paragraph on page 2 with following:

In the chip ~~size thus determined~~ sized as described above, the active region 21 surrounded by the I/O region 23 is a region where circuits can be actually placed. When circuits designed to fit in the active region 21 ~~is~~ are placed, the circuits are formed over the entire active region 21.

Replace the second paragraph of the "SUMMARY OF THE INVENTION" section with following:

In the semiconductor device thus configured, a no-patterned region having no circuit mounted therein is utilized in the active region where circuits can be mounted, and a plurality of logic circuits having functions identical to or different from those of logic circuits mounted in the remaining active region ~~is~~ are mounted in the no-patterned region. Consequently, the device can be shipped as a product if at least one of the logic circuits operates normally to significantly improve and more effectively utilize the semiconductor device.

Replace the second paragraph of the "DESCRIPTION OF THE PREFERRED EMBODIMENTS" section with the following:

Arranged in the I/O region 12 are a plurality of input/output pads 14 which are electrodes for connecting lead-out terminals for a logic LSI with a circuit inside the semiconductor chip through bonding wire. Each of

the input/output pads 14 is ~~shaped to have a square~~ shaped with a side of having sides approximately 100 ~~in~~  $\mu\text{m}$  in length.

Replace the paragraph beginning on line 30 of page 5 with the following:

In Fig. 3, devices other ~~than~~ than the block A and block B and signal lines form a selection circuit for operating the block A or block B and are mounted on the semiconductor chip 10.

Replace the first full paragraph on page 6 with following:

The block A and block B are circuits which operate by connecting their GND terminals to the ground and their  $V_{dd}$  terminals to  $V_{dd}$ . The block A is configured such that the GND terminal is connected to the ground when an N-channel transistor  $T_{na}$  is turned on, and the  $V_{dd}$  terminal is connected to  $V_{dd}$  when a P-channel transistor  $T_{pa}$  is turned on. ~~On the other hand~~ Similarly, the block B is configured such that the GND terminal is connected to the ground when an N-channel transistor  $T_{nb}$  is turned on, and the  $V_{dd}$  terminal is connected to  $V_{dd}$  when a P-channel transistor  $T_{pb}$  is turned on.

Replace the third full paragraph on page 6 with following:

The fuse X and the fuse Y are made, for example, from tungsten or aluminum, and can be blown by a laser beam output from a laser repair apparatus. When the fuse X is blown by a laser beam output from a laser repair apparatus. When the fuse X is blown, the SEL signal is permanently set to LOW level, and when the fuse Y is blown, the SEL signal is permanently set to HIGH level. When both the fuse Y is and the fuse X are blown, the pad PT is released. When neither of the fuse X nor the fuse Y is blown, the SEL signal is set according to the logic level of a signal input from the pad PT.